computed from the data by Guinier approximation, providing also a quality estimate of the data set. Other overall parameters and the characteristic functions are computed, and, for monodisperse systems, particle shape is reconstructed ab initio. All these steps are assembled in a pipeline running completely automatically without user intervention. The summary of the results including plots and models are stored in XML-based format which gives the possibility to conveniently browse and analyze the results. Decision-making blocks are being developed to select proper analysis actions and to compare concurrent models or suggest experiments reducing the ambiguity of the current model.

Keywords: SAXS, automated data collection, automation

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X-ray reflectivity and grazing-incidence small-angle scattering studies of high-k dielectric films

Andrew J. Allen, Martin L. Green
National Institute of Standards and Technology (NIST), Ceramics Division, NIST, stop 8520, 100 Bureau Drive, Gaithersburg, Maryland, 20899, USA, E-mail：andrew.allen@nist.gov

Results will be presented from combined X-ray reflectivity and grazing-incidence small-angle X-ray scattering (GISAXS) studies of the nucleation, growth and internal structure of atomic layer deposited (ALD) hafnium oxide (hafnia) films. ALD is an important film growth technique that enables accurate growth of ultrathin layers (1 nm to 3 nm) for high-k gate dielectric materials such as hafnium oxide. The use of a hafnia layer as the gate dielectric on a silicon substrate will play a critical role in extending Moore’s Law to the next generation of electronic devices. The X-ray reflectivity yields information on the film thickness, surface roughness and hafnia/Si interfacial region, while GISAXS provides complementary information on the film internal structure and also on the surface roughness and hafnia/Si interface. Furthermore, while reflectivity provides out-of-plane structural information, GISAXS also provides information on the in-plane structure. However, with films this thin, both experiments must be conducted at an X-ray synchrotron source in order to access the high scattering vectors (Q) required. Our studies have explored variations in the hafnia film morphology as a function of different chemical preparations in the ALD process, of film thickness, and also of thermal annealing such as can occur in service thermal transients, etc. By combining the reflectivity and GISAXS data with data from other methods such as Rutherford back-scattering, transmission electron microscopy and electrical measurements, new insights can be gained into the integrity and performance of thin ALD hafnia films used in high-k dielectric gate applications.

[1] M.L. Green, A.J. Allen, X. Li, J. Wang, J. Ilavsky, A. Delabie, R. Puurunen and B. Brijs; Appl. Phys. Lett., 88, 032907 (2006).

Keywords: GISAXS, reflectivity, thin films

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Location of Mn sites in GaMnAs thin films studied by means of X ray diffuse scattering

Zbynek K Sourek[1], Milos Kopecky[1], Jiri Kub[1], Edoardo Busetto[2], Andrea Lausi[2], Miroslav Cukr[1], Vit Novak[1], Kamil Olejnik[1]
[1]Institute of Physics AS CR, [2]Sincrotrone Trieste, S. S. 14, km 163.5, 34012 Basovizza; Trieste, Italy, E-mail：sourek@fzu.cz

The ferromagnetic properties of $Ga_{1-x}Mn_xAs$ alloys depend on the sites of Mn dopants. The Curie temperature T_C increases with the concentration of the substitutional Mn cations. On the other hand, T_C is strongly decreased by defects, the most important being Mn interstitials. The sites of Mn impurities in $Ga_{1-x}Mn_xAs$ thin films with different concentrations of Mn were studied by means of the X-ray diffuse scattering. An image of the local neighbourhood of Mn atoms in a $Ga_{1-x}Mn_xAs$ (x=0.02) thin film has been obtained by means of X-ray diffuse scattering holography. The positions of the first and second nearest neighbours of the manganese atoms evidence the Mn atoms in substitutional positions (Fig. 1(left)). Moreover, the changes of the local atomic structure of a $Ga_{1-x}Mn_xAs$ (x=0.07) layer during annealing were studied using X-ray diffuse scattering. The difference of pair-distribution functions before and after annealing (Fig. 1(right)) imaged the fraction of atoms that changed by annealing and identified it to be exclusively interstitial atoms.

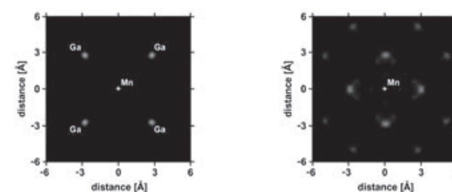

Fig. 1: The local neighbourhood of Mn cations in $Ga_{1-x}Mn_xAs$ thin films with the concentration of Mn (x = 0.02 (left) and (x = 0.07 (right).

Keywords: magnetic semiconductors, X-ray diffuse scattering, holography

P12.09.30

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Structure at Fe/NiO(100) and Fe/MgO(100) interfaces by X-ray absorption fine structure

Federico Boscherini[1], Stefano Colonna[2], Paola Luches[3], Stefania Benedetti[3], Sergio Valeri[3]
[1]University of Bologna, Department of Physics, viale C. Berti Pichat 6/2, Bologna, Bologna, 40127, Italy, [2]CNR Istituto di Struttura della Materia, Via del Fosso del Cavaliere, 00133 Rome, Italy., [3]S3-INFM Dipartimento di Fisica, Universita` di Modena e Reggio Emilia, via G. Campi 213/a, I-41100 Modena, Italy, E-mail：federico.boscherini@unibo.it

Interfaces between ferromagnetic (FM) and antiferromagnetic (AFM) films are extensively studied since they exhibit the intriguing exchange bias effect. On the other hand, the interface formation between a FM film and a non-magnetic (NM) material is an interesting system being the constituting elements in tri-layers showing the magnetoresistance effect. NiO is a very promising AFM material for applications, since its Neel temperature is higher than room temperature and MgO is largely used as a spacer between FM films in spin-valve devices. The FM-AFM and FM-NM interfaces constitute the fundamental elements in the design of new magneto-optical devices. Theoretical models of FM-AFM and FM-NM systems often assume an abrupt interface, which must be verified experimentally since the influence of exact interface structure on the magnetic properties of these systems has been demonstrated to be crucial. We have employed polarization dependent X-ray Absorption Fine Structure (XAFS) at the Fe K-edge to investigate the structure at the Fe/NiO(100) and Fe/MgO(100) interfaces. The XAFS measurements demonstrate that the two interfaces present different structures. Indeed, we find [1] that Fe film at the Fe/NiO(100) interface exhibits a complete tetragonal distortion of the unit cell and demonstrate the formation of a buckled FeO layer with expanded Fe-O distances perpendicular to the growth plane. Instead,

at the Fe/MgO(100) interface do not detect any oxygen diffusion in the Fe film showing a sharp interface with the Fe crystallographic cell tetragonally distorted to match the MgO crystal lattice. These results will be discussed in relation to the magnetic properties of the systems.

[1] P. Luches et al, Phys. Rev. Lett. 96, 106106 (2006).

Keywords: interfaces, X-ray absorption fine structure, thin films

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Surface X-ray diffraction studies of CaF_2(110)/Si(001) interface formation

Takayoshi Shimura[1], Sergey M Suturin[2], Nikolai S Sokolov[2], Alexander G Banshchikov[2], Reginald N Kyutt[2], Osami Sakata[3], Jimpei Harada[4], Masao Tabuchi[5], Yoshikazu Takeda[5]

[1]Osaka Univ., Material & Life Science, 2-1 Yamadaoka, Suita, Osaka, 565-0871, Japan, [2]Ioffe Physical Technical Institute, 26 Polytechnicheskaya str., St. Petersburg, 194021, Russia, [3]Japan Synchrotron Radiation Research Institute (JASRI)/SPring-8, Kouto, Sayo, Hyogo 679-5198, Japan, [4]Rigaku Co., 3-9-12 Matsubara, Akishima, Tokyo 196-8666, Japan, [5]Nagoya Univ., Furo-cho, Chikusa-ku, Nagoya 464-8603, Japan, E-mail：shimura@mls.eng.osaka-u.ac.jp

In the earlier studies [1, 2] it was found that an interface of CaF_2(110)/Si(001) with non-trivial relations was formed during CaF_2 epitaxial growth on Si(001) surface at high temperature. The atomic structure of this interface was related to the formation of the wetting layer consisting of nanostripes running along [110] direction. In order to investigate the structure of the interface *in situ* surface X-ray diffraction (SXRD) measurements were carried out at the BL13XU of SPring-8. CaF_2 of 0.7-2.0 monolayer was grown on Si(001) substrate and over 40 in-plane reflections and 8 fractional order rods were measured. SXRD revealed the 3×1-like surface reconstruction (fig. 1) which is consistent with the electron diffraction studies [2]. A two-dimensional structural model was constructed based on the electron density distribution obtained from in-plane reflectioin data. The intensity profiles along the rods, reflecting the electron density distribution across the interface, suggested that more than one molecular layer were involved in the formation of the interface wetting layer.

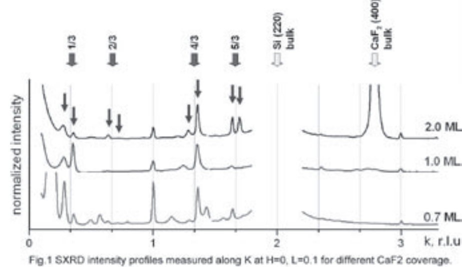

Fig.1 SXRD intensity profiles measured along K at H=0, L=0.1 for different CaF2 coverage.

[1] T. Sumiya et al., Surf. Sci. 376, 192 (1996).
[2] L. Pasquali et al., Phys. Rev. B72, 045448 (2005).

Keywords: surfaces and interfaces, surface diffraction, *in-situ* experiments

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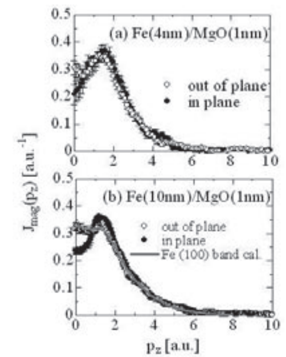
Electroic states at the interface of Fe/MgO magnetic tunneling junction

Hiroshi Sakurai[1], Takuro Tamura[1], Toshitaka Kurachi[1], Satoshi Homma[1], Hiromi Oike[1], Akane Agui[2], Yoshiharu Sakurai[3], Masayoshi Itou[3], Hiromichi Adachi[4], Hiroshi Kawata[4]

[1]Gunma University, Production Science and Technology, 1-5-1 Tenjin-cho, Kiryu, Gunma, 376-8515, Japan, [2]SRRC, JAEA, 1-1-1Kouto, Sayou-gun, Hyogo, 679-5148, Japan, [3]SPring-8/JASRI, 1-1-1Kouto, Sayou-gun, Hyogo, 679-5198, Japan, [4]KEK-PF, 1-1 Oho, Tsukuba, Ibaraki, 305-0801, Japan, E-mail：sakuraih@el.gunma-u.ac.jp

Recently fully epitaxial Fe/MgO/Fe MTJs have the likelihood of an extremely high MR ratio because of the coherent tunneling effect. For conservation of wave function coherency, an electronic structure at the interface is important. In this paper we discuss the electronic states at the interface of Fe/MgO magnetic tunneling junction by measuring magnetic Compton profiles (MCPs). Fe(xnm)/MgO(1nm) (x=4,10) multilayes were fabricated on Si(111) substrates and Al foil substrates by R.F. sputtering. Total thickness was adjusted to about 1000nm. The texture of Fe(200) and MgO(200) was confirmed by XRD measurements. No Fe oxide diffraction peak was observed. Magnetization measurements showed magnetic dead layer of 1nm at the interface. The MCP measurements were carried out at SPring-8-BL08W and KEK-PF-ARNE1A1. Fig.1(a),(b) show the MCPs of the Fe/MgO multilayers. The "hollow" around the pz=0 is deeper in the case of the Fe(4nm)/MgO(1nm) than Fe(10nm)/MgO(1nm). This indicates existence of relatively large spin polarization of conduction electron at the interface and suggests that the spin polarization of conduction electron remain although the Fe3d magnetization disappears.



Keywords: Compton profiles, multilayer films, interface characterization

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Thin film structures of epitaxial chromium on MgO(001) substrates by MBE

Kiyoshi Sakaue, Noriyoshi Tanaka, Isao Takahashi, Hikaru Terauchi

Kwansei Gakuin University, Department of Science and Technology, Gakuen 2 chome 1, Sanda city, Hyogo prefcture, 669-1337, Japan, E-mail：sakaue@kwansei.ac.jp

Thin films of chromium (Cr) were epitaxially grown on MgO(001) substrates by means of molecular beam epitaxy (MBE) and studied by in-situ reflection high energy electron diffraction (RHEED) and ex-situ X-ray diffraction. Depositions of the Cr films were carried out from room temperature to 973K with vacuum of the order of 10-5 Pa. Epitaxial relations of Cr(001)//MgO(001) and Cr[100]//MgO[110] were obtained. We find that Cr(001) layers grown at the temperature higher than 673K and slow deposition rate of 0.1 nm/s shows 2X2 surface reconstructions. Epitaxial growth progressed further, clear horizontally-elongated RHEED streaks were found when the azimuth of the incident electron beam was parallel to the Cr[100] and superposed to usual streak and spotty pattern. Horizontal streaks were observed under following conditions; (1) low deposition rate and (2) high substrate temperature. Horizontal RHEED streaks can be speculated that the Cr thin films have wire-like structures along with [110] direction of Cr layer and was somewhat related to the existence of oxygen in the residual gas. X-ray diffraction from the Cr film, however, revealed that no evidence of chromium oxide, such as Cr_2O_3, was found.